

**AMENDMENTS TO THE CLAIMS**

1. (Currently Amended) A mask comprising ~~a predetermined~~ plural contact hole patterns that form a line, and ~~an~~ plural auxiliary patterns each having an area smaller than the predetermined pattern that of each contact hole pattern,

~~which are arranged so that where a virtual lattice is assumed which has a lattice point located at a center of the predetermined pattern, a center of the auxiliary pattern is offset from the lattice point of the virtual lattice wherein the plural auxiliary patterns include a first auxiliary pattern and a second auxiliary pattern, the first auxiliary pattern having an opening having a center that is aligned with the line, the first auxiliary pattern being located apart from a contact hole pattern at an end of the plural contact hole patterns by a period of the plural contact hole patterns, the second auxiliary pattern having an opening having a center that is offset from the line, and the second auxiliary pattern being equally distant from both the first auxiliary pattern and the contact hole pattern at the end.~~

2. Cancelled.

3. (Currently Amended) A mask according to ~~aspect~~ claim 1, wherein, when an orthogonal virtual lattice having nodes at centers of the plural contact hole patterns is assumed, an offset between a center of the second auxiliary pattern and ~~a corresponding the~~ orthogonal virtual lattice ~~point~~ is 1/6 to 5/6 as long as a period of the orthogonal virtual lattice.

4. (Currently Amended) A mask according to ~~aspect~~ claim 1, wherein, when an orthogonal virtual lattice having nodes at centers of the plural contact hole patterns is assumed, an offset between a center of the second auxiliary pattern and ~~a corresponding the~~ orthogonal virtual lattice ~~point~~ is 1/3 to 2/3 as long as a period of the orthogonal virtual lattice.

5. (Currently Amended) A mask according to ~~aspect~~ claim 1, wherein the second auxiliary pattern has an opening, and at a center of two the orthogonal virtual lattice points in the virtual lattice is located at the opening of the auxiliary pattern.

6-13. Cancelled.

14. (Currently Amended) An exposure method comprising the step of illuminating a mask according to claim 1 by using a light that enables the predetermined plural contact hole patterns to resolve and prevents the plural auxiliary patterns from resolving, and exposing an object using the light from the mask, ~~wherein the mask arranges a predetermined pattern and an auxiliary pattern smaller than the predetermined pattern so that where a virtual lattice is assumed which has a lattice point located at a center of the predetermined pattern, a center of the auxiliary pattern is offset from the lattice point of the virtual lattice.~~

15-16. Cancelled.

17. (Currently Amended) An exposure method according to claim ~~16~~ 14, wherein the effective light source has a dark center portion.

18-19. Cancelled.

20. (Currently Amended) A mask designing method ~~suitable for~~ designing an exposure method for illuminating a mask that includes plural contact hole patterns that form a line, and plural auxiliary patterns each having an area smaller than that of each contact hole pattern, the mask enabling by using light that enables the predetermined pattern plural contact hole patterns to resolve and prevents while preventing the plural auxiliary pattern from resolving, and for exposing an object using the light from the mask via a projection optical system, said mask designing method comprising the steps of:

~~arranging plural auxiliary patterns in a direction other than a periodic direction of the predetermined pattern and other than a direction orthogonal to the periodic direction~~ a first auxiliary pattern having an opening that has a center that is aligned with the line, the first auxiliary pattern being located apart from a contact hole pattern at an end of the plural contact hole patterns by a period of the plural contact hole patterns; and.

arranging a second auxiliary pattern having an opening having a center that is offset from the line, the second auxiliary pattern being equally distant from both the first auxiliary pattern and the contact hole pattern at the end, and the plural auxiliary patterns including the first and second auxiliary patterns.

21. Cancelled.

22. (Currently Amended) A device fabricating method comprising the steps of: exposing an object by using ~~an mask exposure method according to claim 14;~~ and developing the object that has been exposed, ~~wherein a mask arranges a predetermined pattern and an auxiliary pattern smaller than the predetermined pattern so that where a virtual lattice is assumed which has a lattice point located at a center of the predetermined pattern, a center of the auxiliary pattern is offset from the lattice point of the virtual lattice.~~